

10/577938

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of
PHILLIPS et al.

AP20R Rec'd CTM PTO 03 MAY 2006

Atty. Ref.: 124-1158

Serial No. unknown

TC/A.U.: unknown

Filed: May 3, 2006

Examiner: unknown

For: STRAINED SEMICONDUCTOR DEVICES

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May 3, 2006

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO/SB/08a. A copy of the International Search Report, cited foreign patent documents and literature references are attached.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO/SB/08a and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted,

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Sheet 1 of 1

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| INFORMATION DISCLOSURE CITATION | ATTY. DOCKET NO. <u>124-1158</u> | SERIAL NO. <u>10/577938</u> <u>unknown</u> |
| | APPLICANT <u>PHILLIPS et al.</u> | |
| (Use several sheets if necessary) | FILING DATE <u>May 3, 2006</u> | TC/A.U. <u>unknown</u> |

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

| | | | | | | | TRANSLATION | |
|----------|--------------|------|---------|---------|-------|----------|-------------|----|
| DOCUMENT | | DATE | | COUNTRY | CLASS | SUBCLASS | YES | NO |
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*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.